

Diffraction at GaAs/Fe₃Si core/shell nanowires: the formation of nanofacets

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Abstract

GaAs/Fe₃Si core/shell nanowire structures were grown by molecular-beam epitaxy on oxidized Si(111) substrates and characterized by synchrotron x-ray diffraction as well as scanning- and transmission electron microscopy. The surfaces of the original GaAs NWs are completely covered by the ferro-magnetic metal Fe₃Si. The Fe₃Si shells show nanofacets consisting mainly of well pronounced Fe₃Si{111} planes. Density functional theory reveals that the Si-terminated Fe₃Si{111} surface has the lowest energy. We can analyze the x-ray diffuse scattering and diffraction of the ensemble of nanowires avoiding the signal of the substrate and polycrystal films located between the wires. Fe₃Si nanofacets cause streaks in the x-ray reciprocal space map rotated by an azimuthal angle of 30 ° compared with those of bare GaAs nanowires.

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I. INTRODUCTION

Nanowires (NWs) that combine a semiconductor and a ferromagnet in a core/shell geometry have gained a lot of interest in recent years.[1–6] Because of the cylindrical shape of the ferromagnet, such core/shell NWs allow for a magnetization along the wire axis and thus perpendicular to the substrate surface.[7] Ferromagnetic tubes with a magnetization perpendicular to the substrate surface have the potential for circular-polarized light emitting diodes that can optically transmit spin information in zero external magnetic field.[8]

The combination of the binary Heusler alloy Fe_3Si and GaAs, has several advantages compared to most previously studied semiconductor/ferromagnet (SC/FM) core/shell NWs. The lattice matching allows for the molecular beam epitaxy (MBE) of high quality planar hybrid structures.[9–13] In addition, the cubic Fe_3Si phase shows a robust stability against stoichiometric variations, which leads to only slight modification of the magnetic properties.[14] Moreover, the thermal stability against chemical reactions at the SC/FM interface is higher than that of conventional ferromagnets like Fe, Co, Ni, and $\text{Fe}_x\text{Co}_{1-x}$. [9]

The nucleation of planar crystalline films on substrates can be considered in a similar way as wetting or nonwetting of liquids.[15] If the formation of the film surface and the film-substrate interface leads to an surface energy gain $\Delta\gamma < 0$ compared to the bare substrate surface, the film wets the substrate and grows layer-by-layer in Frank van der Merwe growth mode. In case of an surface energy expense ($\Delta\gamma > 0$), three-dimensional (3D) islands form in the Volmer-Weber (VW) growth mode, similar to liquid droplets with a finite contact angle. Fe_3Si is lattice matched to GaAs. Nevertheless we observed the strain-free VW island growth mode of Fe_3Si on GaAs.[16] Thus initially isolated islands can adopt their equilibrium shape before coalescence.

Similarly small particles of Au on a MgO substrate e.g. adopt the equilibrium shape with $\{111\}$ and $\{100\}$ facets.[17] The equilibrium crystal shape of GaAs in an As-rich environment consists of $\{111\}$, $\{110\}$ and $\{100\}$ facets.[18] For the Ga-assisted catalyst-free growth of GaAs NWs by MBE in the $[111]$ direction only the $\{110\}$ sidewalls are present for geometrical reasons, as the growth rate of the NWs along $[111]$ is dominating.[19] However for Au-induced NW growth $\{111\}$ nanofacets were found in the zincblende sections of the NWs.[20] MBE grown GaAs/AlAs core/shell NWs were decorated by Stranski Krastanov (SK) growth of InAs islands.[21] These islands exhibit $\{111\}$ and $\{115\}$ facets and develop

preferentially at the $\langle 112 \rangle$ -oriented corners of the NWs. Ge islands on Si NWs exhibited $\{111\}$, $\{110\}$ and $\{113\}$ facets as a result of a SK growth process.[22] Ferromagnetic MnAs islands grow in a strain driven VW growth mode on semiconducting InAs NWs, where the lattice mismatch amounts up to 18 percent.[23] In our system $\text{Fe}_3\text{Si}/\text{GaAs}$ we can expect a strain-free VW island growth of Fe_3Si on $\text{GaAs}\{110\}$.[16] We recently demonstrated that $\text{GaAs}/\text{Fe}_3\text{Si}$ core/shell NWs prepared by MBE show ferromagnetic properties with a magnetization oriented along the NW axis (i.e. perpendicular to the substrate surface). However, the structural and magnetic properties of the core/shell NWs depend on the substrate temperature T_S during the growth of the Fe_3Si shells.[24] For certain growth temperatures a coincidence of the core- and shell-orientations was observed [25], and the Fe_3Si growth is pseudomorphic on GaAs. In addition nanofacetting of the Fe_3Si shells was found. The GaAs cores are usually not free of defects, especially near the Si/GaAs interface and during the late phase of GaAs NW growth planar defects connected to the transition from zincblende to wurtzite segments are found.[26] In this work, we investigate Fe_3Si shells grown around $\text{GaAs}(111)$ oriented cores at different substrate temperatures T_S and analyze the nanofacets induced by strain-free VW growth of Fe_3Si shells using X-ray diffraction (XRD) in grazing incidence geometry, scanning electron microscopy (SEM), and transmission electron microscopy (TEM).

II. THEORETICAL SECTION

The equilibrium state of the Fe_3Si surface as a function of composition is determined by the minimization of the grand potential Ω ,[27, 28] where E is the energy of the crystal, S and T are the entropy and the temperature of the system, n_i and μ_i are the numbers of atoms of sort i and the corresponding chemical potentials.

$$\Omega = E - TS - \sum n_i \mu_i, \quad (1)$$

This minimization is usually performed for the temperature $T = 0$. In other words the stability of the surface (i.e. its crystallographic orientation and its surface termination or chemical configuration) is given by its surface energy per unit area γ , which is a free energy expressed with respect to the chemical potentials μ_i , which represent reservoirs of

the chemical species involved. This means:

$$\gamma \cdot A = E_t - n_{Fe}\mu_{Fe} - n_{Si}\mu_{Si}, \quad (2)$$

where A is the area of the surface unit cell, E_t is its total energy, and n_{Fe} and n_{Si} are the numbers of Fe and Si atoms in the cell. We assume the surface to be in thermodynamic equilibrium with the bulk material. This implies that $3\mu_{Fe} + \mu_{Si} = g_{Fe_3Si}$, the energy per formula unit of bulk Fe_3Si . [29, 30] This constraint implies that g can be expressed as a function of just one independent variable e.g. μ_{Si} . On the other hand the individual atomic chemical potentials can never exceed the energy of the condensed pure element, i.e. the energy per atom in bulk Fe and bulk Si. The three constraints jointly place an upper and lower limit on μ_{Si} . Density functional theory (DFT) [31–35] in the generalized gradient approximation [36] was applied in order to determine the surface energy of low index surfaces using the Vienna Ab Initio Simulation Package (VASP). [37, 38] The calculations were performed in a slab geometry using slabs from 12 to 16 Å thick and a vacuum region of 10 Å. All atomic positions were relaxed except the innermost 3-4 layers, until the largest force component on every atom was below 0.05 eV Å⁻¹. All of the calculations assumed a fully ordered ferromagnetic Fe_3Si lattice.

III. EXPERIMENTAL SECTION

GaAs/ Fe_3Si core/shell NW structures were grown by MBE on Si(111) substrates. First, GaAs NWs are fabricated by the Ga-assisted growth mode on Si(111) substrates covered with a thin native oxide layer. The growth mechanism is the vapor-liquid-solid (VLS) mechanism, [39–43] where pin holes in the SiO_2 serve as nucleation sites. [44] A Ga droplet is the preferred site for deposition from the vapor. The GaAs NW then starts to grow by preferential nucleation at the spatially restricted GaAs/Si interface. The GaAs NWs are grown at a substrate temperature of 580 °C, with a V/III flux ratio of unity and an equivalent two-dimensional growth rate of 100 nm/h. Once the GaAs NW templates are grown, the sample is transferred under ultra high vacuum conditions to an As free growth chamber for deposition of the ferromagnetic films. There the GaAs NW templates are covered with Fe_3Si shells at substrate temperatures varying between 100 °C and 350 °C. More details regarding the growth conditions can be found in Ref. [7].

The resulting core/shell NW structures were characterized by SEM, X-ray diffraction, and TEM. The X-ray experiments were performed in grazing incidence geometry at the beamline BM 02 of the European Synchrotron Radiation Facility (ESRF) in Grenoble. The energy of the beam was 10 keV and the detector was an area detector S70 from Imxpad. The detector size is 560×120 pixels of size $130 \times 130 \mu\text{m}^2$ each. In order to minimize the penetration depth into substrate and parasitic film between the NWs a very small angle of incidence of 0.04° was chosen.[45] In this way the signal of the ensemble of NWs was always dominating the diffraction pattern. This was checked by observation of the vanishing signal of the single-crystal Si substrate, which would dominate the diffraction curve at larger angles of incidence.

The TEM specimens are prepared by mechanical lapping and polishing, followed by argon ion milling according to standard techniques. TEM images are acquired with a JEOL 3010 microscope operating at 300 kV. The cross-section TEM methods provide high lateral and depth resolutions on the nanometer scale. It has to be considered that TEM imaging of NWs corresponds to two-dimensional projections along electron beam direction.

IV. RESULTS AND DISCUSSION

In SEM micrographs a relatively low area density of well oriented NWs of $\sim 5 \times 10^8 \text{ cm}^{-2}$ is found. In 1 SEM top views of a GaAs core NW and a GaAs/Fe₃Si core/shell NW ($T_S = 200^\circ\text{C}$) are given together with a side-view of a core/shell NW. Regular step patterns, facets, are clearly visible on the sidewalls of the NW. At the top of the NW a thinner part is visible. During the last stage of GaAs NW growth no Ga is supplied, and so the remaining Ga in the droplet on top of the NWs is consumed, leading to an elongation of the NW at reduced diameter. In addition 1 illustrates the orientation of the $\{11\bar{1}\}$ shell facets with respect to the cores. A hexagonal prism symbolizing the GaAs NWs with $\langle 110 \rangle$ -oriented sidewalls is drawn schematically. In addition a tetrahedron depicting the equilibrium shape of Fe₃Si crystallites consisting of Fe₃Si $\{11\bar{1}\}$ planes is shown. The tilted Fe₃Si $\{11\bar{1}\}$ planes form extended shell facets. These facets are intersecting the top Fe₃Si(111) plane, which is parallel to the substrate surface. This results in the formation of triangular features at the top which are observed by SEM.

2 (a) depicts the XRD curves of the $(\bar{2}20)$ reflection of GaAs/Fe₃Si core/shell NWs,

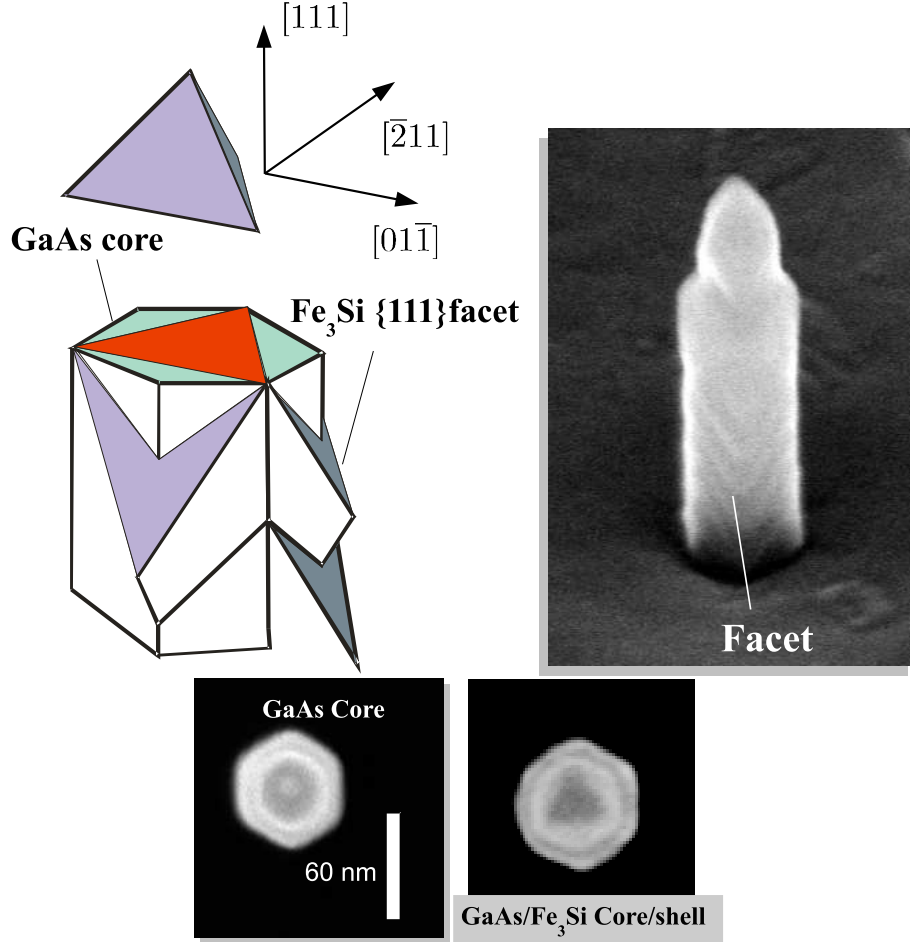


Figure 1. (color online) SEM side view of a core/shell NW (right side) and SEM top views of a core and core/shell NWs (below) grown at $T_S = 200$ °C. A sketch of the GaAs core and the Fe_3Si shells (left side) with tilted $\{11\bar{1}\}$ facets is illustrating schematically the orientation relationship between the cores and the facets. In addition a tetrahedron consisting of $\{111\}$ planes is given.

$T_S = 200$ °C. A radial $\omega/2\theta$ -scan (thick line) along the $[\bar{1}10]$ direction and an angular ω -scan perpendicular to the $[\bar{1}10]$ direction (thin line), together with their full widths at half maximum (FWHM) are given. The radial scan shows thickness fringes (marked by arrows) corresponding to a thickness of 14.3 nm equal to the Fe_3Si shell thickness (cf. 4 (b)). The radial scan has a FWHM of 0.08° whereas the angular scan has a larger width of 0.55° . The FWHM in angular direction here corresponds to the range of twist of the NWs, as in-plane reflections are used.[46] The range of tilt of GaAs NWs was measured to be near $(0.28 \pm 0.1)^\circ$ using symmetrical out-of-plane measurements.

2 (b) and (c) show XRD curves of GaAs/ Fe_3Si core/shell NWs, $T_S = 200$ °C. Radial $\omega/2\theta$ -

scans along (b) the $\langle 110 \rangle$ and (c) the $\langle 211 \rangle$ directions are given. Scan (b) does not reveal any unexpected maxima due to polycrystalline material whereas scan (c) exhibits additional maxima caused by the wurtzite regions in the GaAs cores. Merely the (400) maximum points to another orientation of some of the crystallites probably caused by additional twins in the cores that are not parallel to the GaAs/Si interface. The detection of the wurtzite regions in the GaAs cores again points to the fact, that our measurements are sensitive for the core/shell NWs only. In a similar scan for a sample grown at 300 °C we observed diffraction maxima evidencing chemical reaction between cores and shells.

3 demonstrates in-plane reciprocal space maps of the $(\bar{2}20)$ -reflection of GaAs NWs (left) and GaAs/Fe₃Si core/shell NWs (center and right) grown by MBE on a Si(111) substrate. The growth temperatures of the Fe₃Si shells were 200 °C (center) and 300 °C (right). The crystallographic directions are sketched below. The radial direction ($\omega/2\Theta$) of the scans is vertical and the angular direction (ω) horizontal. The facets of the pillar shaped cores with hexagonal cross section are clearly distinguished by streaks in the diffuse scattering pointing along the $\langle 110 \rangle$ directions. Remarkably, in the central map core streaks along the $\langle 110 \rangle$ directions are still visible although they are superimposed by additional streaks along the $\langle 1\bar{2}1 \rangle$ directions originating from the facets of the Fe₃Si shells. In the map shown on the right side only streaks of the shell facets remain. Additional maxima above the main peak indicate chemical reactions between Fe₃Si and GaAs occurring at $T_S = 300$ °C near the interface similar as those observed for planar films on GaAs.[9, 47]

4 shows a multi-beam bright-field TEM micrograph, illustrating the orientations of the Fe₃Si facets of the core/shell NW on Si(111). In 4(a) the incident electron beam is oriented along $[1\bar{1}0]$ in (b) along $[11\bar{2}]$. In (a) we observe facets of the Fe₃Si shell in (b) we see smooth interfaces and surfaces. The roughening due to the facetting is not observed along this direction. The visibility of the thickness fringes in 2 points to the fact, that (1) we really measure the diffraction signal of the core/shell NWs only, and (2) that the thickness fringes are measured in an ($\omega/2\Theta$)-scan along the $[1\bar{1}0]$ direction where the interfaces are smooth. A growth temperature of 200 °C results in this highly perfect Fe₃Si shell structure.

The $(11\bar{1})$ surface nanofacets are expected to be inclined to the (110) cladding planes of the GaAs cores leading to an increase of the surface area A. There is a non negligible material transport over distances small compared to the NW lengths. On a larger length-scale the Fe₃Si shell is approximately reproducing the shape of the GaAs core NWs.[24] The

straight horizontal contrasts in the GaAs cores in (a) are caused by planar defects leading to alternating zincblende and wurtzite GaAs regions.

5 shows results of DFT calculations of surface energies of the Fe₃Si shells for a wide range of chemical potentials and several possible surface terminations. Fe₃Si surfaces were found to be Si-rich.[48, 49] In that case the Si-terminated Fe₃Si(111) planes are most favorable energetically, even if geometrical factors, i.e. the inclination angle between GaAs(110) and Fe₃Si(111) planes of $\psi = 35.3^\circ$, are taken into account. The (110) surface has an energy of $\gamma_{110} = 140 \text{ meV}\cdot\text{\AA}^{-2}$. Hence the criterion for (111) facet formation is that the (111) surfaces have an energy less than $\gamma_{110} \cdot \cos(\psi) = 114.25 \text{ meV}\cdot\text{\AA}^{-2}$. As a result our DFT calculations confirmed that the formation of facets reduces the overall surface energy.

V. CONCLUSIONS

Layer-by-layer growth could in principle solve the problem of nanofacetting. However, even planar Fe₃Si grows on GaAs(001) in the strain-free VW island growth mode.[16] Poor wetting during the nucleation of Fe₃Si on GaAs leads initially to isolated islands, despite of perfect lattices match. We supported the hypothesis that the nanofaceted Fe₃Si shells found in the present work are a result of VW island growth. The role of the surface is more important for NWs than for planar films, the faceted growth of the lattice matched shells is an example for such surface related phenomena. Facetting will also play a role in systems with SK growth mode and strain-driven VW island growth.

GaAs core NWs were grown on the oxidized Si(111) surface inside holes of the SiO₂ film via the VLS growth mechanism. Then ferromagnetic Fe₃Si shells were grown resulting in continuous covering of the cores. A polycrystal film grew unintentionally between the NWs. We have successfully avoided the XRD signal of the polycrystal film by studying the ensemble of core/shell NWs using x-ray grazing incidence diffraction geometry. We did not observe additional orientations of the shell with respect to the core, i.e. the shells are pseudomorphic. Up to a growth temperature of 200 °C additional broadening of the shell diffraction maxima compared to those of the cores is rather limited. The analysis of the x-ray diffuse scattering revealed the hexagonal cross-section of the GaAs cores. In addition Fe₃Si nano-facets of the shells cause streaks rotated by an azimuthal angle of 30 °. The nano-facets consist e.g. of {111} planes tilted around ⟨011⟩ axes towards the ⟨211⟩ direction, i.e. for

[111] oriented NWs the $(\bar{1}11)$ facets are most pronounced, forming a regular pattern along the GaAs NWs. The $\{111\}$ facets of Fe_3Si are formed because under our Si-rich conditions they have the lowest surface energy in agreement with the DFT calculations.

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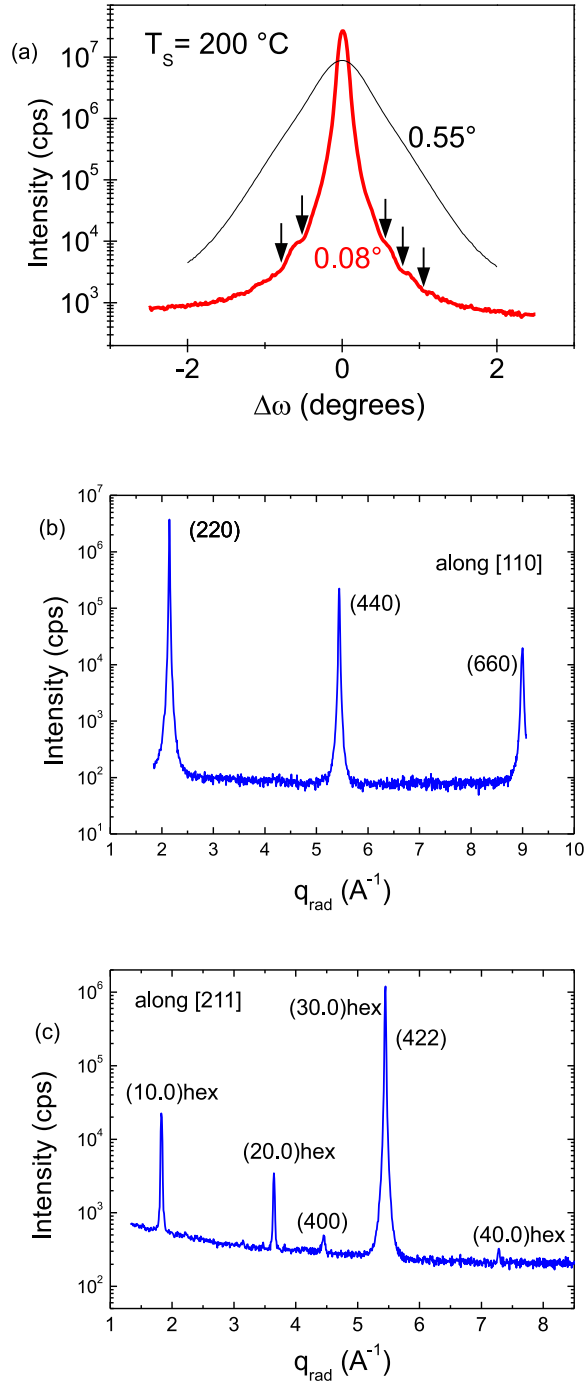


Figure 2. (color online) (a) XRD curves of the $(\bar{2}20)$ reflection of GaAs/Fe₃Si core/shell NWs, $T_S = 200$ °C. A radial $\omega/2\theta$ -scan (thick red line) along the $[\bar{1}10]$ direction and an angular ω -scan perpendicular to the $[\bar{1}10]$ direction (thin black line), together with their full widths at half maximum (FWHM) are given. Thickness fringes are marked by arrows. (b) and (c) radial XRD $\omega/2\theta$ -scans along $\langle 110 \rangle$ (b) and $\langle 211 \rangle$ (c) over a wider range than (a).

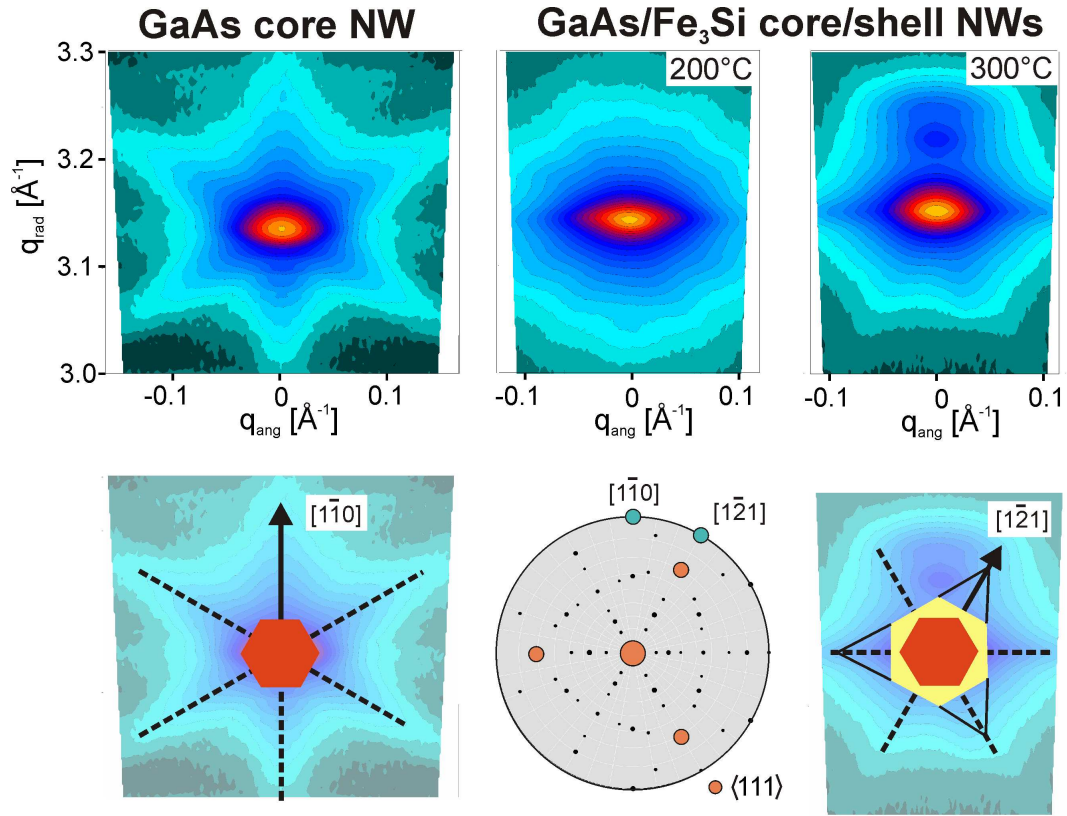


Figure 3. (color online) $(\bar{2}20)$ in-plane reciprocal space maps of $[111]$ -oriented GaAs NWs (upper left) and GaAs/Fe₃Si core/shell NWs (upper center and upper right) grown by molecular beam epitaxy on Si(111). The growth temperatures of the Fe₃Si shells are given above. The crystallographic directions together with the corresponding sidewalls are sketched below. In the symbolic stereogram (middle) the $[1\bar{1}0]$ and $[1\bar{2}1]$ directions are marked by blue circles and the different $\{111\}$ directions by red circles. The radial direction of the scans is drawn vertically and the angular direction is directed horizontally in the figure.

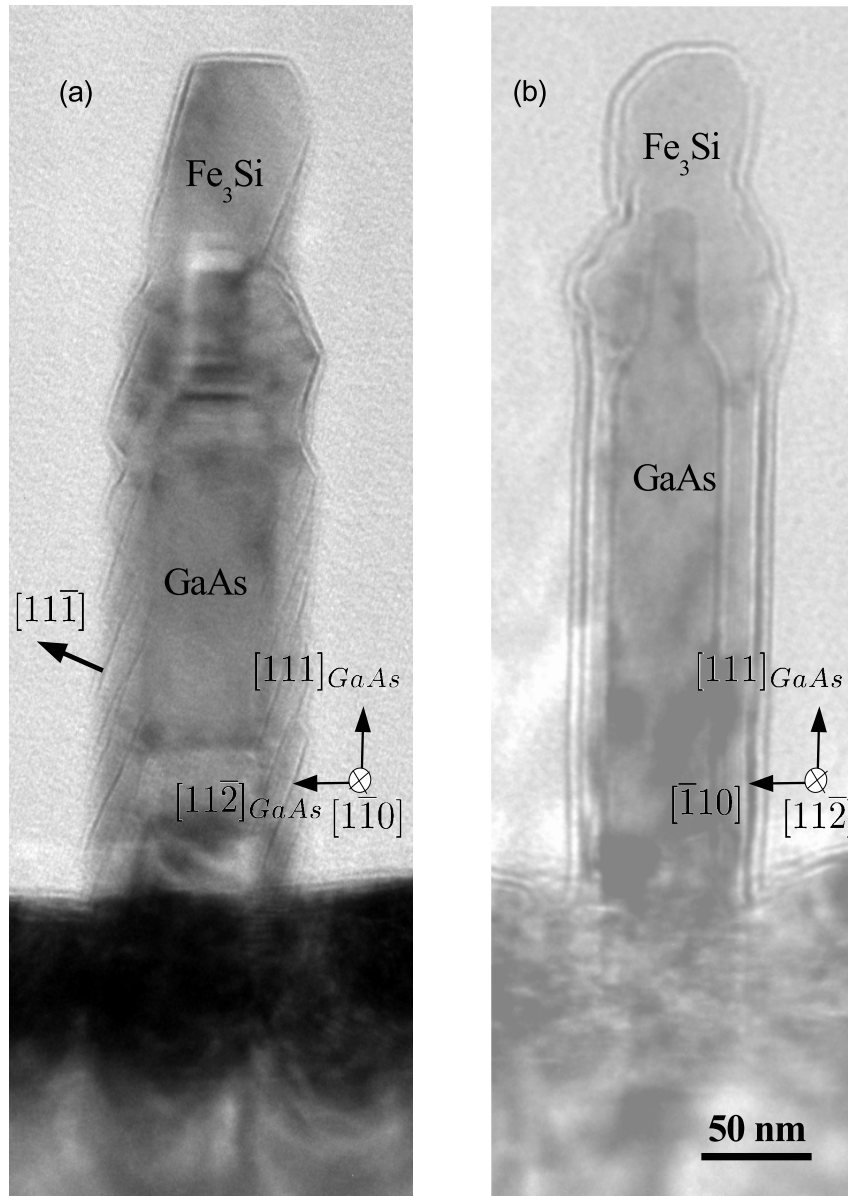


Figure 4. Multi-beam bright-field TEM micrographs illustrating the orientations of the Fe₃Si shell facets with respect to the GaAs cores. The cores and shells are distinguished clearly. For the $[1\bar{1}0]$ direction of the electron beam (a) we see facets corresponding to tilted $(11\bar{1})$ planes as sketched in 1. When the electron beam is running along the $[11\bar{2}]$ direction no facets are observed (b). The images are slightly defocused in order to increase the contrast of the surfaces and interfaces.

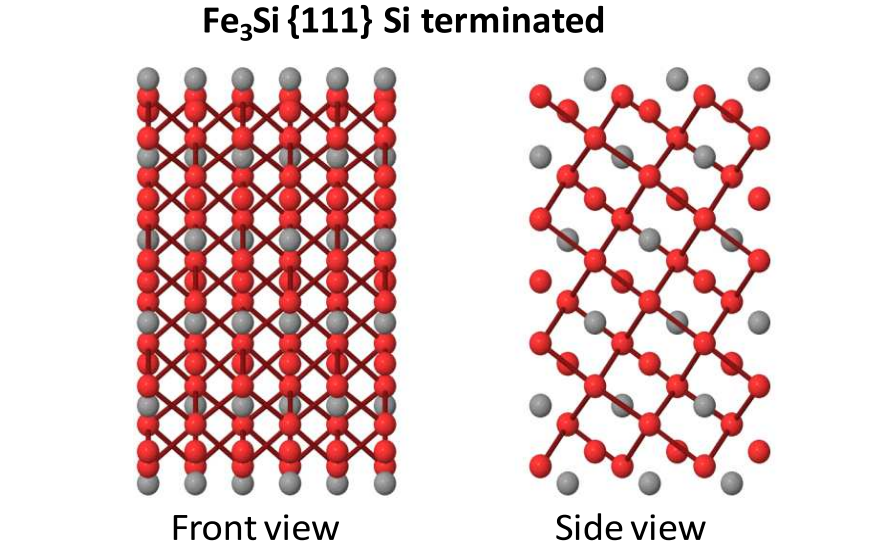
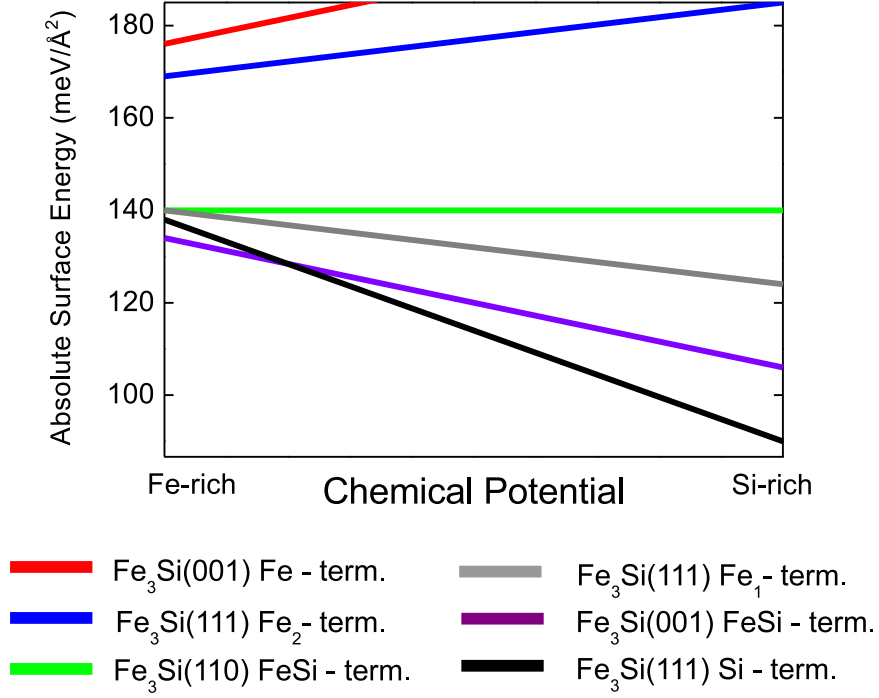


Figure 5. (color online) Surface energy of differently terminated (term.) surfaces calculated by DFT in generalized gradient approximation. The structure of the Si-terminated Fe₃Si{111} surface is illustrated below, Fe atoms are symbolized as red balls whereas Si atoms as grey balls.